

#### Description

The RK002BMT116 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

#### **General Features**

 $V_{DS}$  = 60V I<sub>D</sub> =0.3A

 $R_{DS(ON)} < 2\Omega @ V_{GS}=10V$ 

ESD Rating: HBM≥2000V

#### Application

Battery protection

Load switch

Uninterruptible power supply

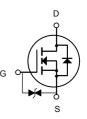
#### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
R <b>K</b> 002BMT116	SOT-23	72K/7002	3000

#### Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
Vds	Drain-Source Voltage		60	V
Vgs	Gate-Source Voltage		±20	V
		T <sub>A</sub> =25℃	0.3	
ID	Continuous Drain Current (TJ =150℃)	T <sub>A</sub> =100℃	0.19	A
lом	Drain Current-Pulsed (Note 1)		0.8	А
PD	Maximum Power Dissipation		0.35	W
Tj,Tstg	Operating Junction and Storage Temperature Range		-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		350	°C <b>/W</b>





N-Channel MOSFET



### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	60	68	-	V
Zero Gate Voltage Drain Current	ldss	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	±100 ±4	±500 ±10	nA uA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.7	1.2	1.9	V
		V <sub>GS</sub> =5V, I <sub>D</sub> =0.1A	-	1.3	3	Ω
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =10V, I <sub>D</sub> =0.3A	-	1	2	Ω
Forward Transconductance	grs	V <sub>DS</sub> =10V,I <sub>D</sub> =0.2A	0.1	-	-	S
Input Capacitance	C <sub>lss</sub>		-	21	50	PF
Output Capacitance	Coss	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V, F=1.0MHz	-	11	25	PF
Reverse Transfer Capacitance	Crss	1 1.000112	-	4.2	5	PF
Turn-on Delay Time	td(on)		-	10	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =30V,I <sub>D</sub> =0.2A	-	50	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =10V, $R_{GEN}$ =10 $\Omega$	-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =10V,I <sub>D</sub> =0.3A, V <sub>GS</sub> =4.5V	-	1.7	3	nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	A

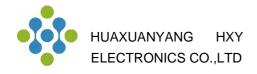
#### Notes:

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



## **Typical Electrical And Thermal Characteristics**

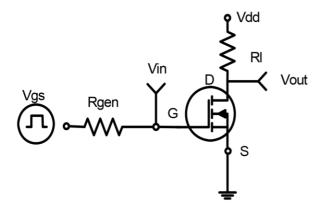
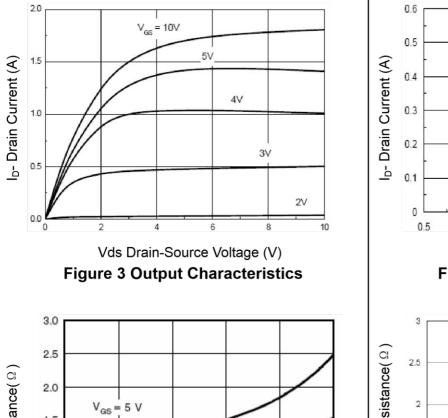


Figure 1:Switching Test Circuit



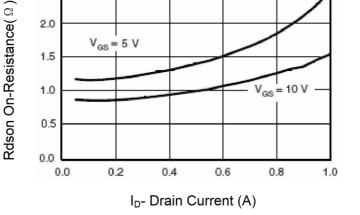


Figure 5 Drain-Source On-Resistance

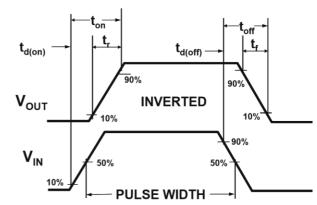


Figure 2:Switching Waveforms

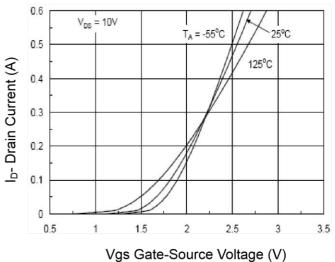
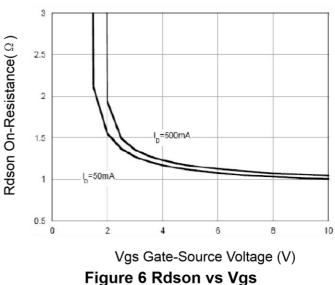
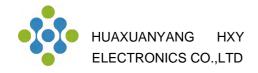
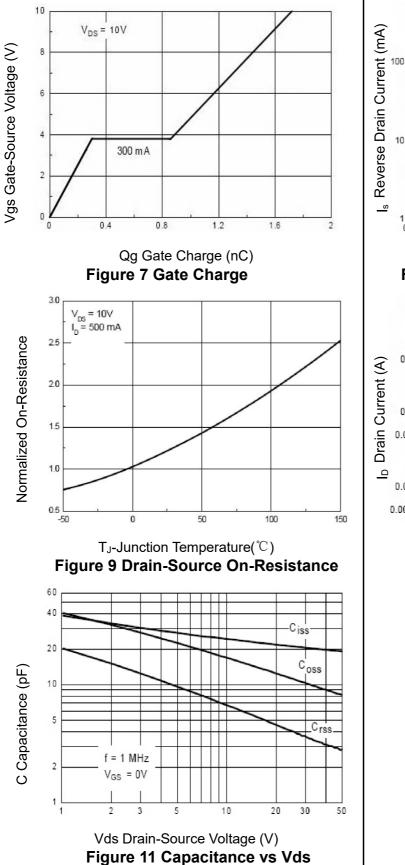


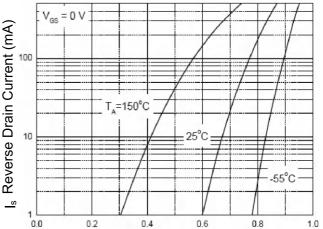
Figure 4 Transfer Characteristics



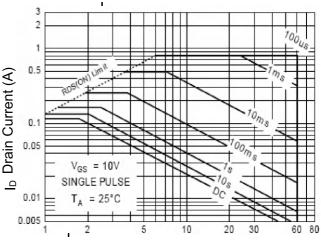


# RK7002BMT116 N-Channel Enhancement Mode MOSFET





Vsd Source-Drain Voltage (V) Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V) Figure 10 Safe Operation Area



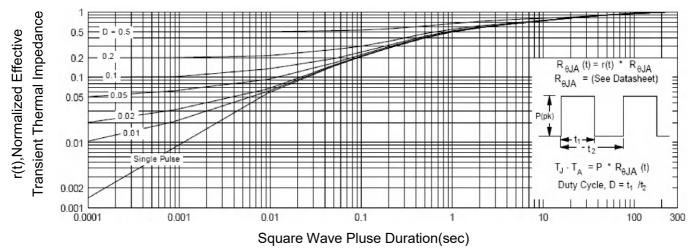
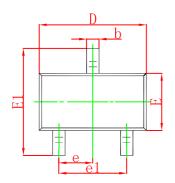
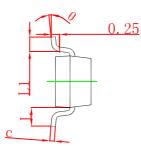


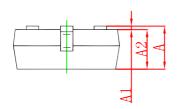
Figure 12 Normalized Maximum Transient Thermal Impedance



## **SOT-23 Package Outline Dimensions**

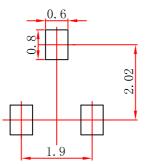






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	) TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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